Atsushi Kawaharazuka

List of Publications by Year
in descending order

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27	155	1163117 8	1281871 11
papers	citations	h-index	g-index

28	28	28	168
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Investigation of CuGaSe2/CuInSe2 double heterojunction interfaces grown by molecular beam epitaxy. AIP Advances, 2015, 5, 027120.	1.3	9
2	Optical properties of Al Ga1â^'As/GaAs superlattice solar cells. Journal of Crystal Growth, 2015, 425, 333-336.	1.5	1
3	Study of single crystal CuInSe2 thin films and CuGaSe2/CuInSe2 single quantum well grown by molecular beam epitaxy. Journal of Crystal Growth, 2015, 425, 203-206.	1.5	7
4	High absorption efficiency of AlGaAs/GaAs superlattice solar cells. Japanese Journal of Applied Physics, 2015, 54, 052301.	1.5	5
5	Photoluminescence study of Si doped and undoped Chalcopyrite CuGaSe2 thin films. Applied Physics A: Materials Science and Processing, 2013, 113, 257-261.	2.3	8
6	Characteristics of CuGaSe2 layers grown on GaAs substrates. Journal of Crystal Growth, 2013, 378, 154-157.	1.5	7
7	High-Absorption-Efficiency Superlattice Solar Cells by Excitons. Japanese Journal of Applied Physics, 2013, 52, 112302.	1.5	4
8	Successful growth of Cu2Se-free CuGaSe2 by migration-enhanced epitaxy. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2012, 30, .	1.2	10
9	Excitonic absorption on AlGaAs/GaAs superlattice solar cells. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 330-333.	0.8	2
10	Effect of Excitons in AlGaAs/GaAs Superlattice Solar Cells. Japanese Journal of Applied Physics, 2011, 50, 052302.	1.5	4
11	Growth of CuGaSe₂ Layers on Closely Lattice-Matched GaAs Substrates by Migration-Enhanced Epitaxy. Japanese Journal of Applied Physics, 2011, 50, 125502.	1.5	8
12	Effect of surface Ga accumulation on the growth of GaN by molecular beam epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 342-346.	0.8	6
13	Magnetic Properties of Multiply Mn Î´-Doped GaAs. Japanese Journal of Applied Physics, 2009, 48, 113001.	1.5	0
14	Investigation of C60Epitaxial Growth Mechanism on GaAs Substrates. Japanese Journal of Applied Physics, 2009, 48, 025502.	1.5	7
15	RHEED intensity oscillation of C60 layer epitaxial growth. Journal of Crystal Growth, 2009, 311, 2227-2231.	1.5	8
16	MBE growth of GaN on MgO substrate. Journal of Crystal Growth, 2007, 301-302, 478-481.	1.5	12
17	Characteristics of multivalent impurity doped C60 films grown by MBE. Journal of Crystal Growth, 2007, 301-302, 687-691.	1.5	6
18	Magnetic and Electric Field Effects of Photoluminescence of Excitons Bound to Nitrogen Atom Pairs in GaAs. Japanese Journal of Applied Physics, 2004, 43, L756-L758.	1.5	0

#	Article	IF	Citations
19	Spin-Polarized Electron Injection through an Fe/InAs Junction. Japanese Journal of Applied Physics, 2003, 42, L87-L89.	1.5	20
20	Field Effect of Photoluminescence from Excitons Bound to Nitrogen Atom Pairs in GaAs. Japanese Journal of Applied Physics, 2002, 41, 5503-5506.	1.5	1
21	Study of free GaAs surfaces using a back-gated undoped GaAs/AlGaAs heterostructure. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 663-666.	2.7	7
22	Electrical Spin Injection from Ferromagnetic Metals into GaAs. , 2002, , 95-106.		5
23	Backgated layers and nanostructures. Physica E: Low-Dimensional Systems and Nanostructures, 2001, 11, 155-160.	2.7	1
24	Transport characteristics of electrons in weak short-period two-dimensional potential arrays. Applied Physics Letters, 2001, 79, 427-429.	3.3	1
25	Formation of a two-dimensional electron gas in an inverted undoped heterostructure with a shallow channel depth. Journal of Applied Physics, 2000, 87, 952-954.	2.5	15
26	Electric Field Induced Recombination Centers in GaAs. Japanese Journal of Applied Physics, 1998, 37, 1622-1625.	1.5	0
27	Optical Properties of Amorphous and Nanostructure Si/SiO₂ Quantum Wells. Journal of Nano Research, 0, 26, 59-62.	0.8	1